Schottky barrier diode

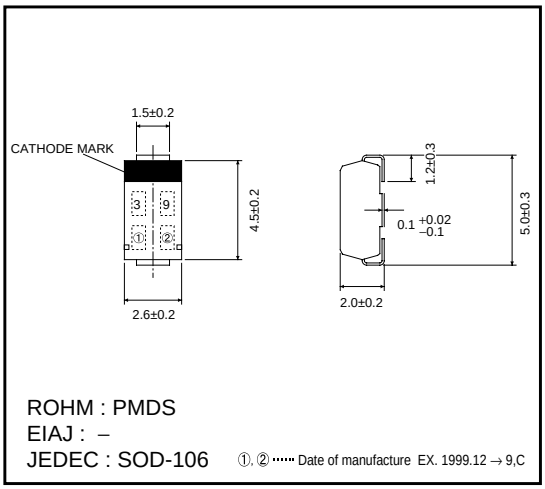
RB081L-20

●**Applications**
High frequency rectification
For switching power supply

●**Features**
1) Compact power mold type. (PMDS)
2) Ultra low V_F.(V_F=0.27V Typ. at 1A)
3) I_O=5A guaranteed despite the size.

●**Construction**
Silicon epitaxial planar

●**External dimensions** (Units : mm)



●**Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
Mean rectifying current	I_O1 *1	5	A
	I_O2 *2	4	A
Peak forward surge current (60Hz 1 ∽)	I_{FSM}	70	A
Junction temperature	Tj	125	˚C
Storage temperature	Tstg	–40~+125	˚C

*1 When mounted on an alumina substrates (82×30×1.0mm), Tc Max.=90˚C
*2 When mounted on an alumina substrates (82×30×1.0mm), Ta=25˚C

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	0.45	V	I_F=5.0A
Reverse current	I_R	–	0.7	mA	V_R=20V

●**Electrical characteristics curves** (Ta=25°C)

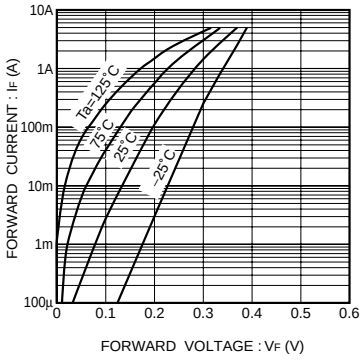


Fig.1 Forward characteristics

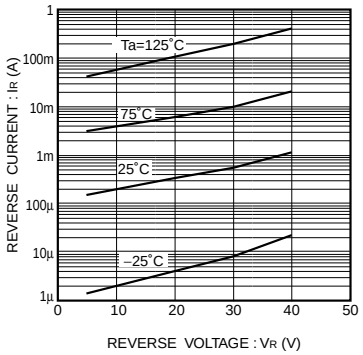


Fig.2 Reverse characteristics

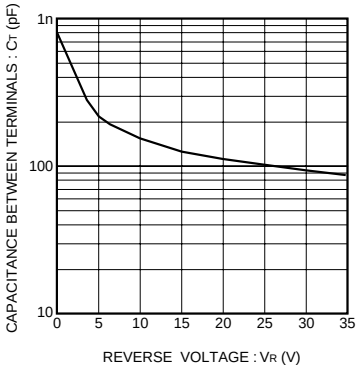


Fig.3 Capacitance between terminals characteristics

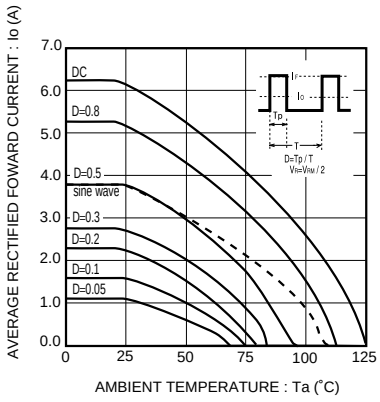


Fig.4 Derating curve (Io-Ta)

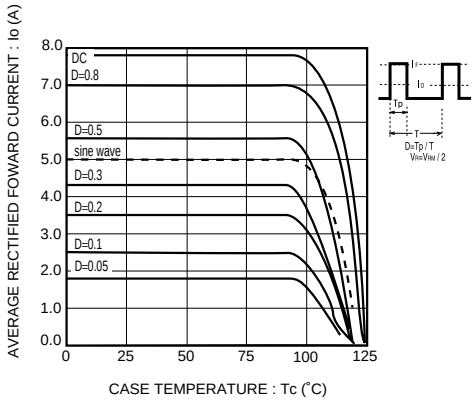


Fig.5 Derating curve (Io-Tc)